

P-Channel 12-V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)
- 12	0.028 at V _{GS} = - 4.5 V	- 6	15.5 nC
	0.039 at V _{GS} = - 2.5V	- 6	
	0.054 at V _{GS} = - 1.8 V	- 6	

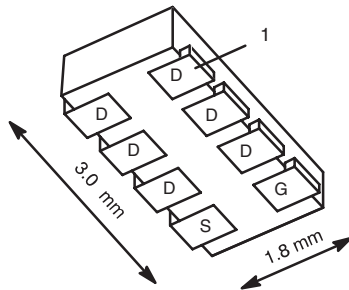
FEATURES

- TrenchFET[®] Power MOSFET: 1.8 V Rated

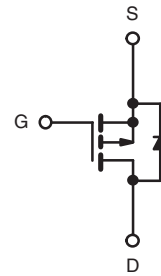
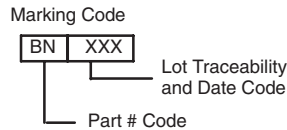


RoHS
COMPLIANT

1206-8 ChipFET[®]



Bottom View



P-Channel MOSFET

Ordering Information: Si5475BDC-T1-E3 (Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	- 12	V	
Gate-Source Voltage	V _{GS}	± 8		
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	A	
		T _C = 70 °C		
		T _A = 25 °C		
		T _A = 70 °C		
Pulsed Drain Current	I _{DM}	- 20	A	
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C		
		T _A = 25 °C		
Maximum Power Dissipation	P _D	T _C = 25 °C	W	
		T _C = 70 °C		
		T _A = 25 °C		
		T _A = 70 °C		
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C	
Soldering Recommendations (Peak Temperature) ^{d, e}		260		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, f}	R _{thJA}	40	50	°C/W	
Maximum Junction-to-Foot (Drain)	R _{thJF}	15	20		

Notes:

- Package limited.
- Surface mounted on 1" x 1" FR4 board.
- t = 5 s.
- See Solder Profile (<http://www.vishay.com/ppg?73257>). The 1206 ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is 95 °C/W.



SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	- 12			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\text{ }\mu\text{A}$		- 7		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			2.5		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	- 0.45		- 1.0	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -12\text{ V}, V_{GS} = 0\text{ V}$			- 1	μA
		$V_{DS} = -12\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$			- 5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq 5\text{ V}, V_{GS} = -4.5\text{ V}$	- 20			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -5.6\text{ A}$		0.023	0.028	Ω
		$V_{GS} = -2.5\text{ V}, I_D = -4.7\text{ A}$		0.032	0.039	
		$V_{GS} = -1.8\text{ V}, I_D = -1.9\text{ A}$		0.044	0.054	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -6\text{ V}, I_D = -6.9\text{ A}$		22		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = -6\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		1400		pF
Output Capacitance	C_{oss}			370		
Reverse Transfer Capacitance	C_{rss}			260		
Total Gate Charge	Q_g	$V_{DS} = -6\text{ V}, V_{GS} = -8\text{ V}, I_D = -6\text{ A}$		26	40	nC
		$V_{DS} = -6\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -6\text{ A}$		15.5	24	
Q_{gs}			2.1			
Q_{gd}			4.0			
Gate Resistance	R_g	$f = 1\text{ MHz}$		9		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -6\text{ V}, R_L = 0.97\text{ }\Omega$ $I_D \cong -6.2\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\text{ }\Omega$		10	15	ns
Rise Time	t_r			38	60	
Turn-Off Delay Time	$t_{d(off)}$			62	95	
Fall Time	t_f			70	105	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -6\text{ V}, R_L = 0.97\text{ }\Omega$ $I_D \cong -6.2\text{ A}, V_{GEN} = -8\text{ V}, R_g = 1\text{ }\Omega$		5	10	
Rise Time	t_r			15	25	
Turn-Off Delay Time	$t_{d(off)}$			65	100	
Fall Time	t_f			72	110	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			- 5.2	A
Pulse Diode Forward Current	I_{SM}				- 20	
Body Diode Voltage	V_{SD}	$I_S = -6.2\text{ A}, V_{GS} = 0\text{ V}$		- 0.9	- 1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -6.2\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		45	70	ns
Body Diode Reverse Recovery Charge	Q_{rr}			27	42	nC
Reverse Recovery Fall Time	t_a			15		ns
Reverse Recovery Rise Time	t_b			30		

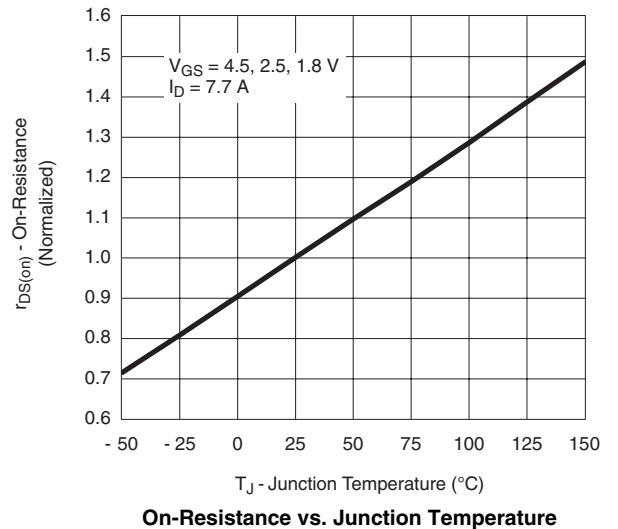
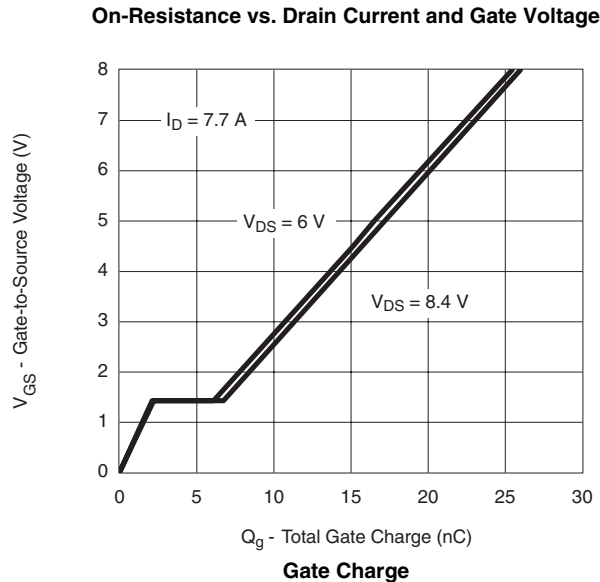
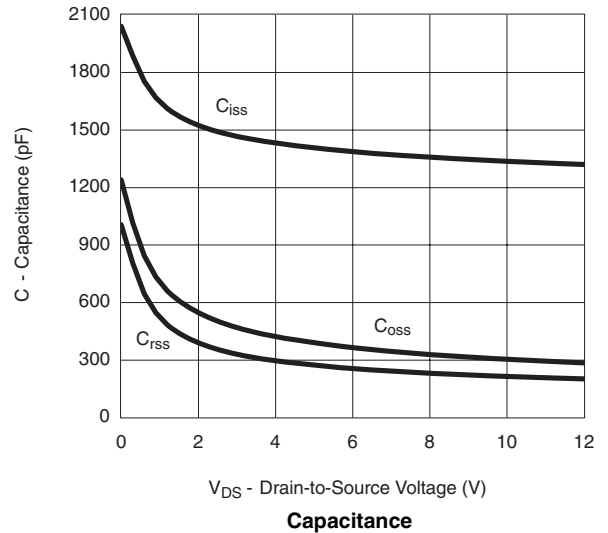
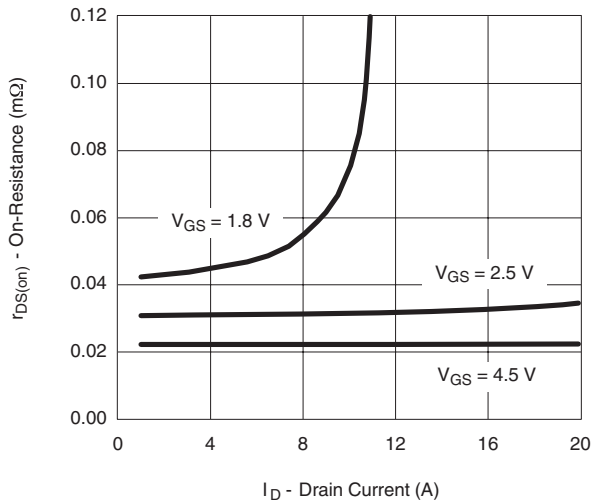
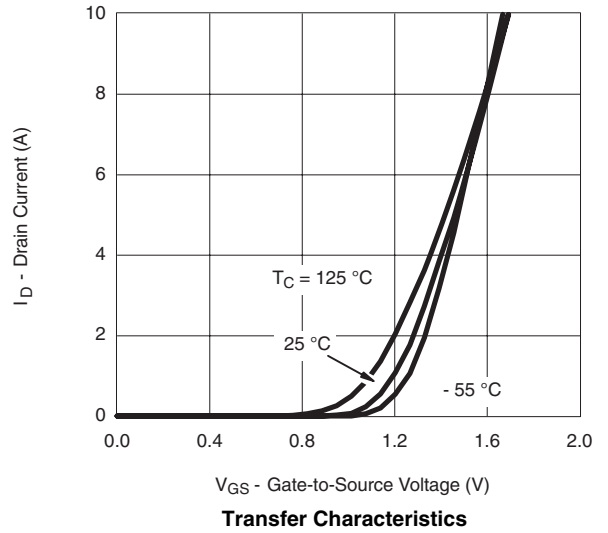
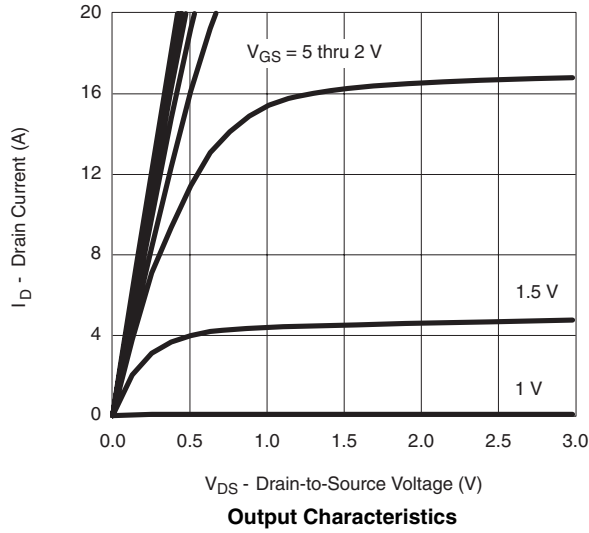
Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

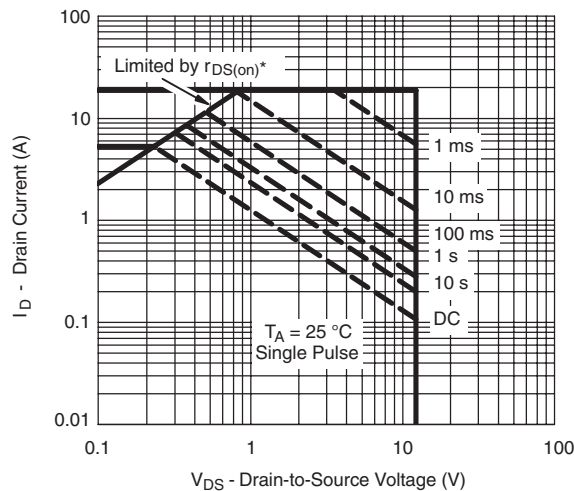
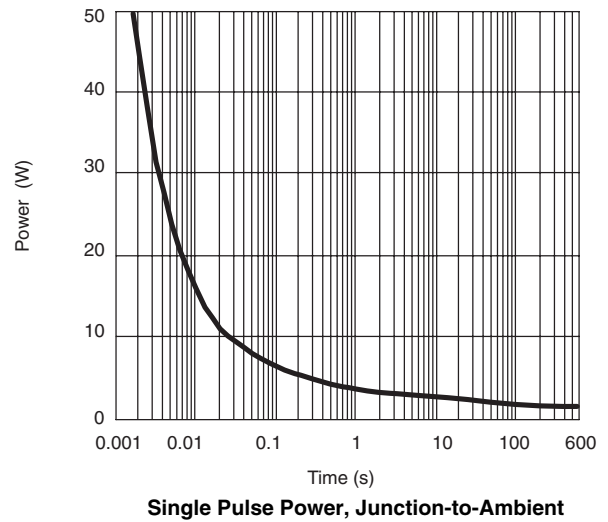
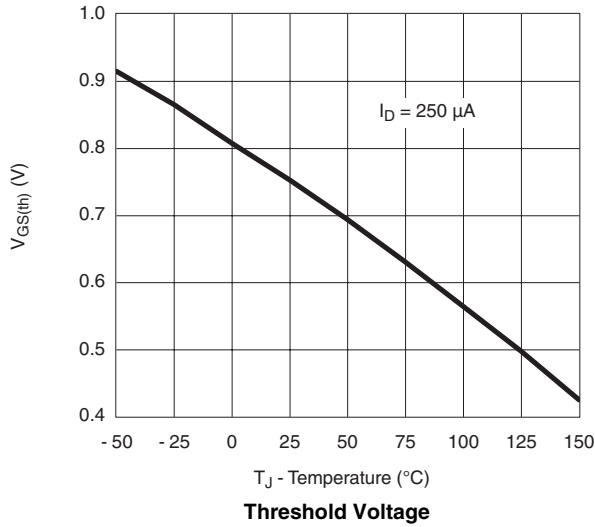
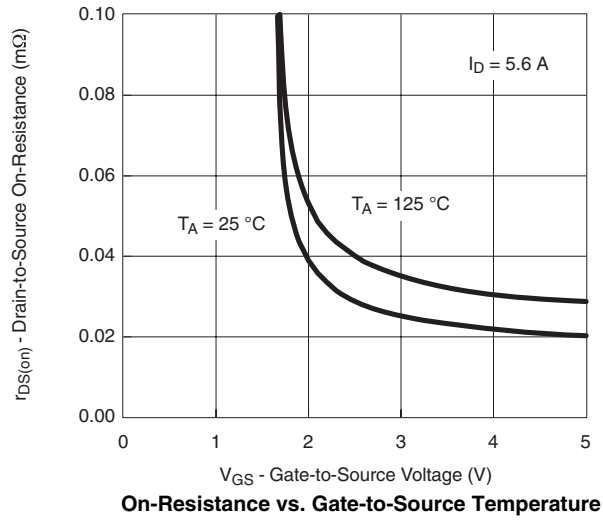
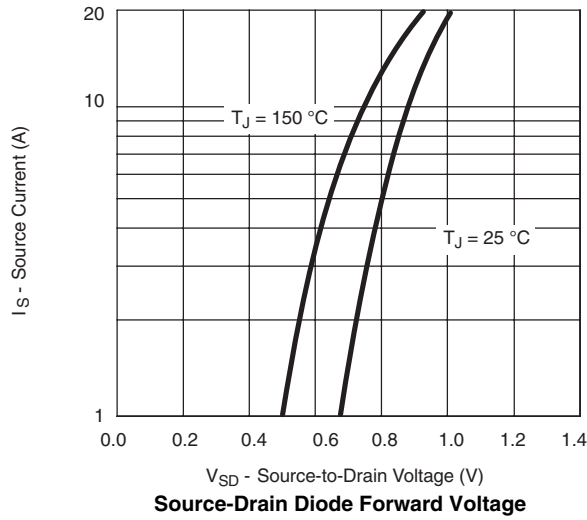


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





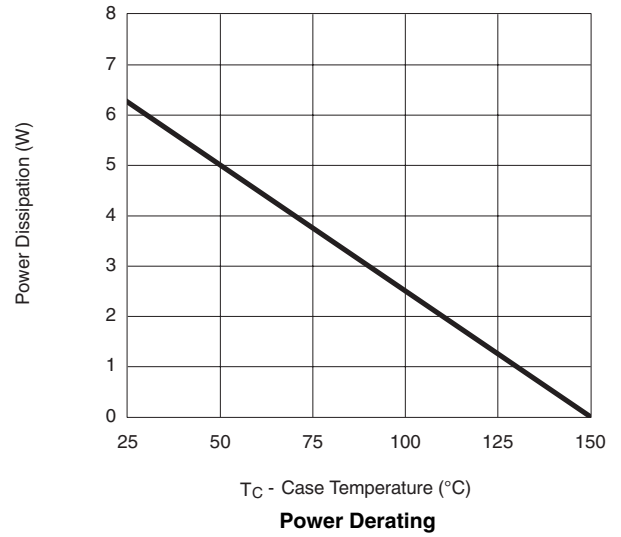
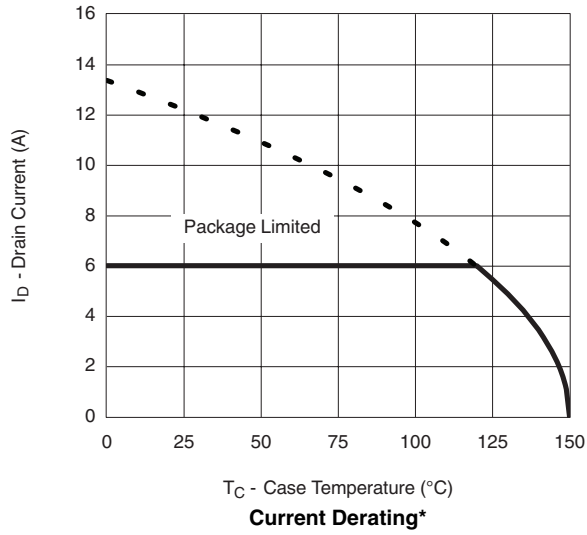
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* $V_{GS} >$ minimum V_{GS} at which $r_{DS(on)}$ is specified

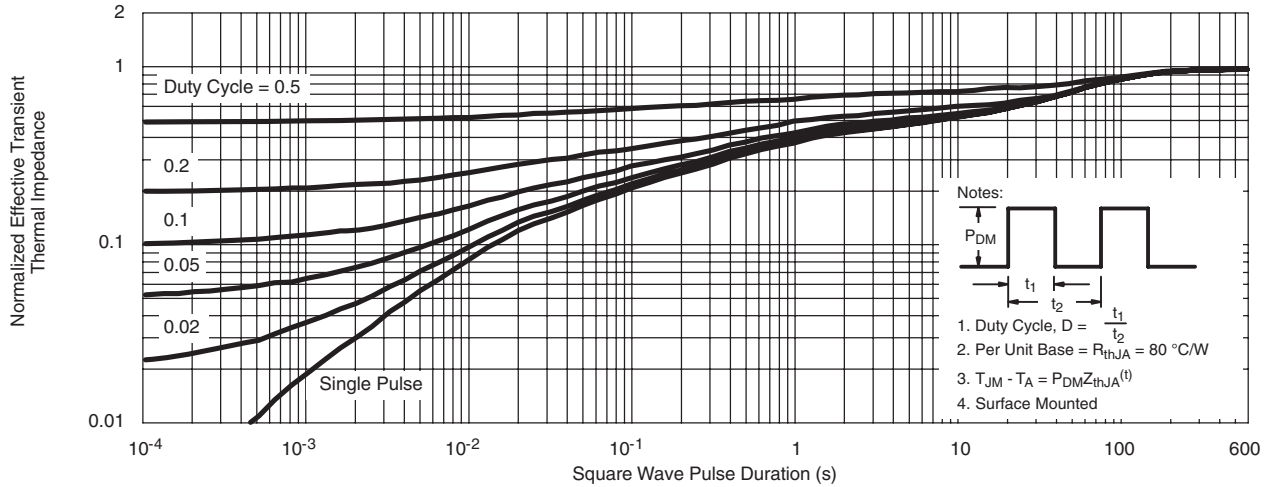


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

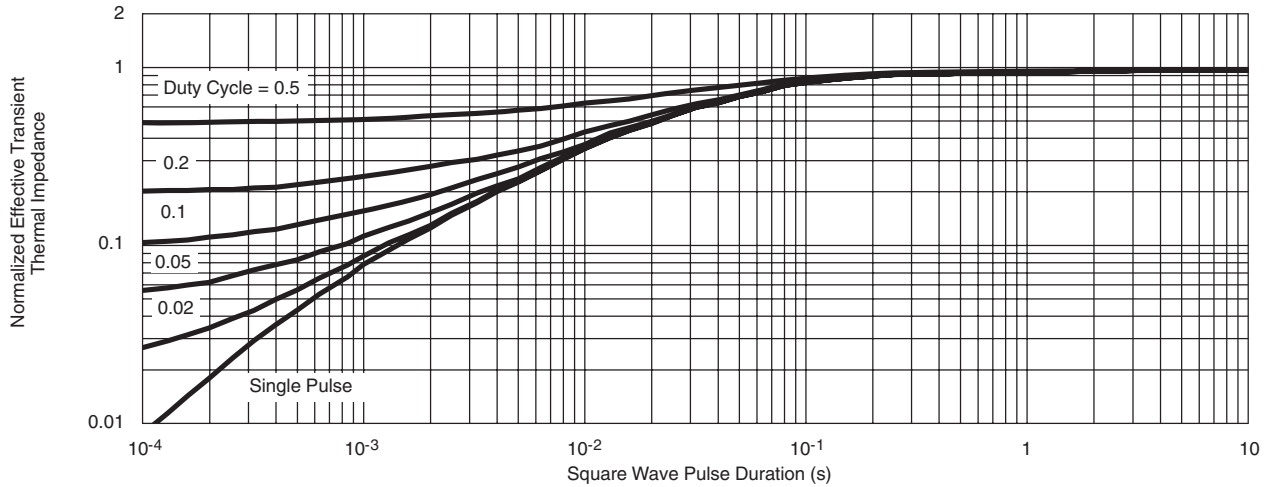


* The power dissipation P_D is based on $T_{J(max)} = 150\text{ °C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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